

### INCHANGE SEMICONDUCTOR

## isc N-Channel MOSFET Transistor

### 10N50

#### DESCRIPTION

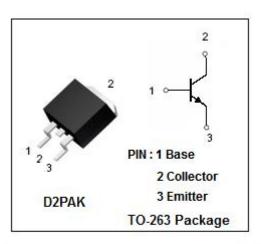
- Drain Current –I\_D=10A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V<sub>DSS</sub>= 500V(Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

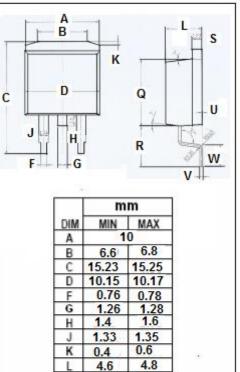
#### APPLICATIONS

• Designed for applications such as switching regulators, switching converters,motor drivers,relay drivers and drivers for power bipolar switching transistors requiring High speed and low gate drive power

#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT					
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	500	V					
V <sub>GS</sub>	Gate-Source Voltage	±20	V					
ID	Drain Current-continuous@ TC=25℃	10	А					
P <sub>tot</sub>	Total Dissipation@TC=25°C	120	W					
Tj	Max. Operating Junction Temperature	150	°C					
T <sub>stg</sub>	Storage Temperature Range	torage Temperature Range -55~150						
THERMAL CHARACTERISTICS								
SYMBOL	PARAMETER	МАХ	UNIT					
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	0.83	°C/W					





8.69

5.28

1.26

0.0

0.37

2.80

Q

R

SU

v

W

8.71

5.30

1.28

0.2

0.39

2.82

isc website: www.iscsemi.cn



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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	450			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =0.25mA	2		4	V
R <sub>DS(on)</sub>	Drain-Source On-stage Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 10A			0.6	Ω
I <sub>GSS</sub>	Gate Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
IDSS	Zero Gate Voltage Drain Current	V <sub>DS</sub> =500V; V <sub>GS</sub> = 0			1	uA
$V_{\text{SD}}$	Forward On-Voltage	I <sub>S</sub> = 10A; V <sub>GS</sub> =0			1.4	V
C <sub>ISS</sub>	Input capacitance				3000	pF
Coss	Output capacitance	V <sub>DS</sub> =25V;			600	pF
C <sub>RSS</sub>	Reverse transfer capacitance				200	pF

#### • ELECTRICAL CHARACTERISTICS (Tc=25°C)

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